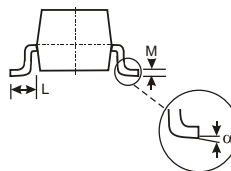
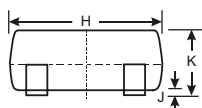
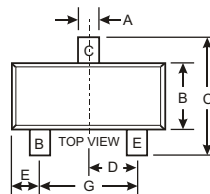


Features

- Ideally Suited for Automatic Insertion
- Epitaxial Planar Die Construction
- For Switching, AF Driver and Amplifier Applications
- Complementary PNP Types Available (BC807)



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°
All Dimensions in mm		

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	50	V
Collector Emitter Voltage	V_{CEO}	45	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	500	mA
Power Dissipation	P_{tot}	300	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 55 to + 150	$^\circ\text{C}$

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C = 10\mu\text{A}$, $I_E = 0$	50			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C = 10\text{mA}$, $I_B = 0$	45			V
Emitter-base breakdown voltage	V_{EBO}	$I_E = 1\mu\text{A}$, $I_C = 0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 45\text{V}$, $I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 4\text{V}$, $I_C = 0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 1\text{V}$, $I_C = 100\text{mA}$	100		600	
	$h_{FE(2)}$	$V_{CE} = 1\text{V}$, $I_C = 500\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}$, $I_B = 50\text{mA}$			0.7	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500\text{mA}$, $I_B = 50\text{mA}$			1.2	V
Base-emitter voltage	V_{BE}	$V_{CE} = 1\text{V}$, $I_C = 500\text{mA}$			1.2	V
Collector capacitance	C_{ob}	$V_{CB} = 10\text{V}$, $f = 1\text{MHz}$		10		pF
Transition frequency	f_T	$V_{CE} = 5\text{V}$, $I_C = 10\text{mA}$, $f = 100\text{MHz}$	100			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	BC817-16	BC817-25	BC817-40
Range	100-250	160-400	250-600
Marking	6A	6B	6C

TYPICAL TRANSIENT CHARACTERISTICS

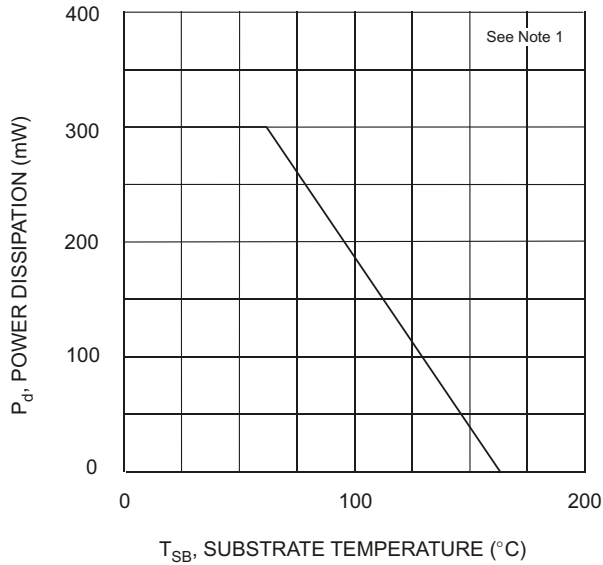


Fig. 1, Power Derating Curve

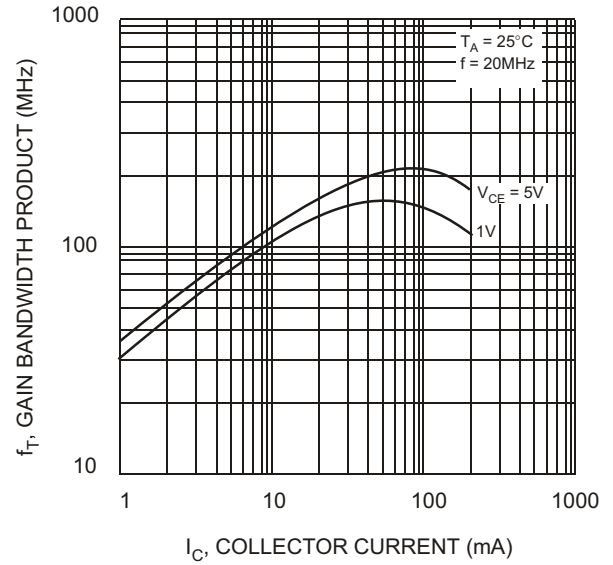


Fig. 2, Gain-Bandwidth Product vs Collector Current

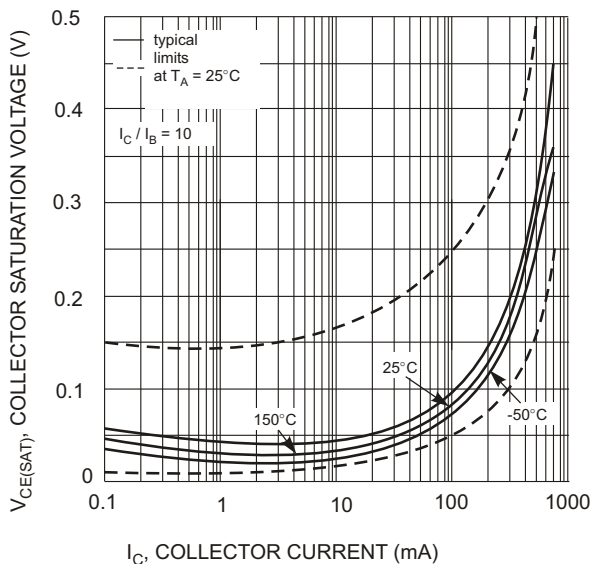


Fig. 3, Collector Sat. Voltage vs Collector Current

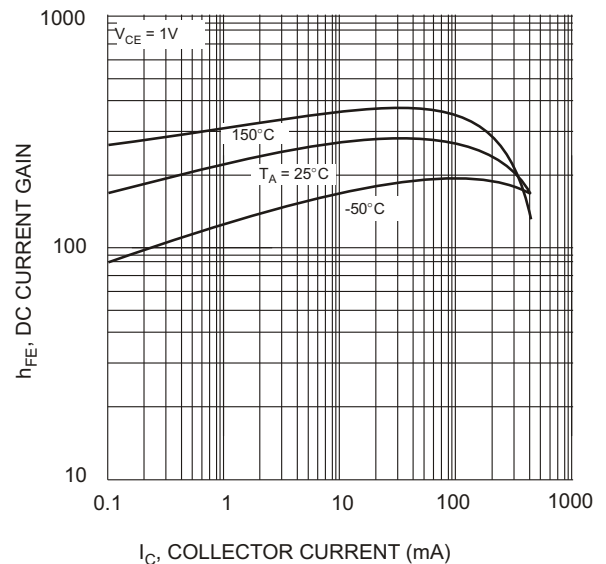


Fig. 4, DC Current Gain vs Collector Current

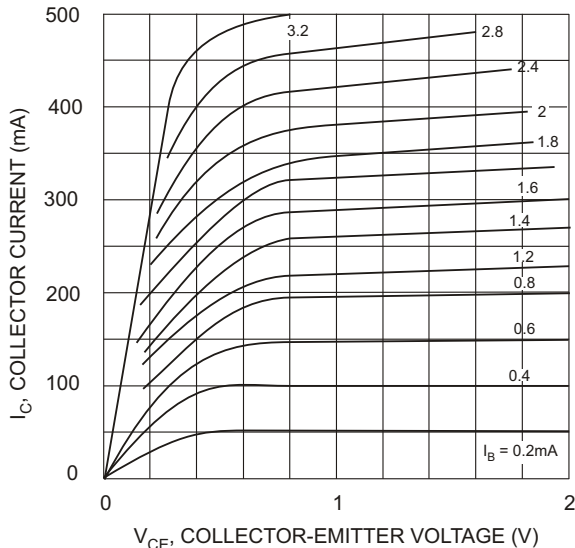


Fig. 5, Typical Emitter-Collector Characteristics

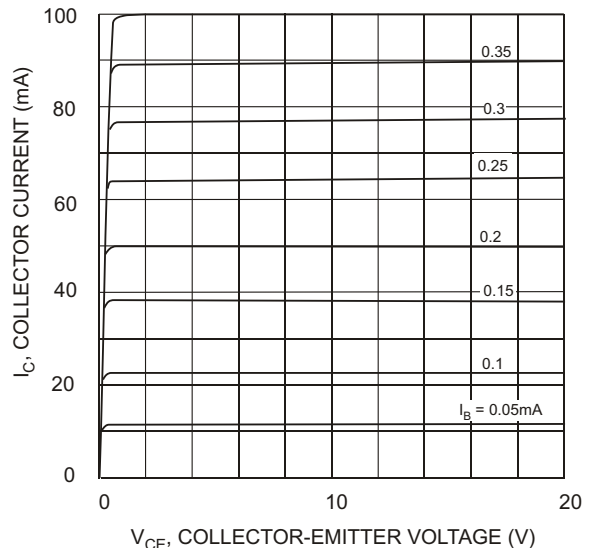


Fig. 6, Typical Emitter-Collector Characteristics

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